Solid State Devices, Inc.
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Phone: (562) 404-7855 * Fax: (562) 404-1773
ssdi@ssdi-power.com * www.ssdi-power.com

SFT2369A2
Series

Dual Microminiature Package
100 mA 15 Volts
Dual NPN Transistor

DESIGNER'S DATA SHEET

Part Number / Ordering Information [1/]

SFT2369A2

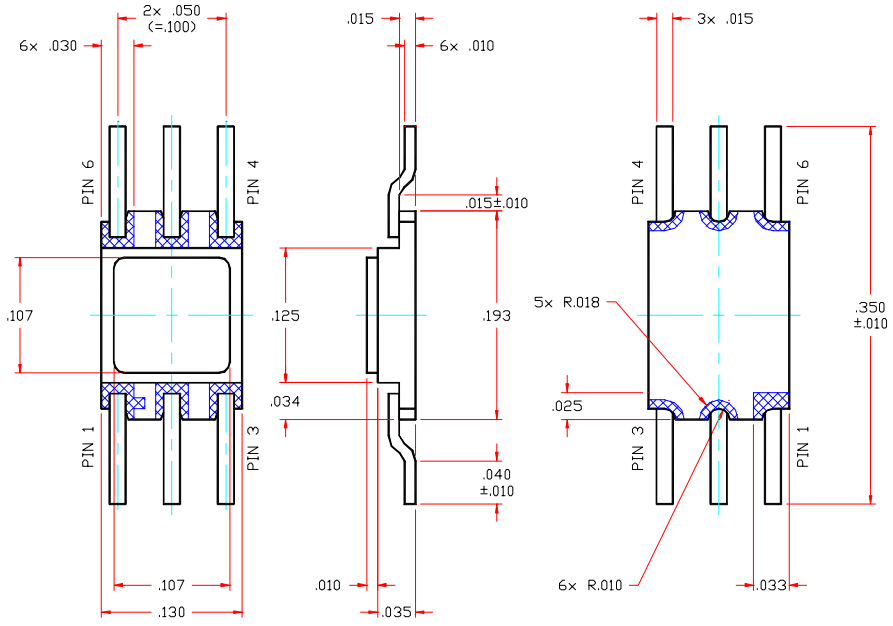
Screening [2/] __ = Commercial
TX = TX Level
TXV = TXV Level
S = S Level

Package GW = Gullwing

Features:
- High Speed Switching Transistor
- Suitable in chopper, uhf and rf application
- Multiple Devices Reduce Board Space
- Replacement for 2N2369AU
- TX, TXV, S-Level screening available

Maximum Ratings		Symbol	Value	Units
Collector – Emitter Voltage		V_{CEO}	15	Volts
Collector – Base Voltage		V_{CBO}	40	Volts
Emitter – Base Voltage		V_{EBO}	4.5	Volts
Continues Collector Current		I_C	100	mAmps
Power Dissipation @ Ta = 25ºC	Per Device Total	P_D	360 500	mW
Operating & Storage Temperature		Top & Tstg	-65 to +200	ºC
Maximum Thermal Resistance (Junction to PCB)		$R_{\theta J\text{-}PCB}$	290	ºC/W

Gullwing (GW)



NOTE: All specifications are subject to change without notification.
SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: TR0045A

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SFT2369A2 Series

Electrical Characteristic [4]		Symbol	Min	Max	Units
Collector – Emitter Sustaining Voltage	I_C = 10 mA	BV_{CEO}	15	—	Volts
Collector Cutoff Current	Vce = 20 V,	I_{CES}	—	400	nA
Collector Cutoff Current	Vcb = 32 V Vcb = 40 V Vcb = 20 V, Ta = 150 ºC	I_{CBO}	—	200 10 30	nA µA µA
Emitter Cutoff Current	Veb = 4.0 V Veb = 4.5 V	I_{EBO}	—	250 10	nA uA
DC Forward Current Transfer Ratio *	V_{CE} = 0.35V, I_C = 10 mA V_{CE} = 0.40V, I_C = 30 mA V_{CE} = 1.0V, I_C = 10 mA V_{CE} = 1.0V, I_C = 100 mA Vce = 1.0V, Ic = 10 mA, Ta= -55 ºC	H_{FE}	40 30 40 20 20	120 120 120 120 —	
Collector – Emitter Saturation Voltage *	I_C = 10mA, I_B = 1.0mA I_C = 30mA, I_B = 3.0mA I_C = 100mA, I_B = 10mA I_C = 10mA, I_B = 1.0mA, Ta= 125 ºC	$V_{CE(Sat)}$	— — — —	0.20 0.25 0.45 0.30	Volts
Base – Emitter Saturation Voltage *	I_C = 10mA, I_B = 1.0mA I_C = 30mA, I_B = 3.0mA I_C = 100mA, I_B = 10mA I_C = 10mA, I_B = 1.0mA, Ta= -55 ºC I_C = 10mA, I_B = 1.0mA, Ta= 125 ºC	$V_{BE(Sat)}$	0.7 — 0.8 — 0.59	0.85 0.9 1.2 1.02 —	Volts
Frequency Transition	V_{CE} = 10V, I_C = 10mA	f_T	500	1000	MHz
Output Capacitance	V_{CE} = 5V, f = 1MHz	c_{ob}	—	4.0	pF
Input Capacitance	V_{CE} = 0.5V, f = 1MHz	c_{ib}	—	5.0	pF
Switch Times Test Circuit per MIL-PRF-19500/317		**ton** **toff** **ts**	— —	12 18 13	nsec

NOTES:

* Pulse Test: Pulse Width = 300µsec, Duty Cycle = 2%

1/ For Ordering Information, Price, and Availability Contact Factory.

2/ Screening per MIL-PRF-19500

3/ For Package Outlines Contact Factory.

4/ Unless Otherwise Specified, All Electrical Characteristics @25ºC.

Available Part Numbers:

SFT2369A2GW

PIN ASSIGNMENT						
Package	**Pin 1**	**Pin 2**	**Pin 3**	**Pin 4**	**Pin 5**	**Pin 6**
GW	Collector1	Base1	Emitter1	Collector2	Base2	Emitter2